# FDD6682/FDU6682

## 30V N-Channel PowerTrench® MOSFET

### General Description

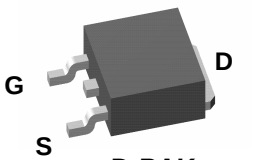
This N-Channel MOSFET has been designed specifically to improve the overall efficiency of DC/DC converters using either synchronous or conventional switching PWM controllers. It has been optimized for low gate charge, low $R_{DS(ON)}$ and fast switching speed.

### Applications

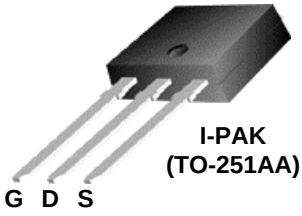
- DC/DC converter
- Motor Drives

### Features

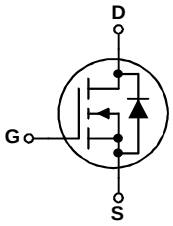
- 75 A, 30 V $R_{DS(ON)}$ = 6.2 mΩ @ $V_{GS}$ = 10 V
  $R_{DS(ON)}$ = 8.0 mΩ @ $V_{GS}$ = 4.5 V
- Low gate charge
- Fast switching
- High performance trench technology for extremely low $R_{DS(ON)}$




D-PAK
(TO-252)




I-PAK
(TO-251AA)




## Absolute Maximum Ratings

$T_A$=25°C unless otherwise noted

| Symbol | Parameter | | Ratings | Units |
|---|---|---|---|---|
| $V_{DSS}$ | Drain-Source Voltage | | 30 | V |
| $V_{GSS}$ | Gate-Source Voltage | | ±20 | |
| $I_D$ | Drain Current – Continuous | (Note 3) | 75 | A |
| | – Pulsed | (Note 1a) | 100 | |
| $P_D$ | Power Dissipation for Single Operation | (Note 1) | 71 | W |
| | | (Note 1a) | 3.8 | |
| | | (Note 1b) | 1.6 | |
| $T_J$, $T_{STG}$ | Operating and Storage Junction Temperature Range | | –55 to +175 | °C |

## Thermal Characteristics

| | | | | |
|---|---|---|---|---|
| $R_{\theta JC}$ | Thermal Resistance, Junction-to-Case | (Note 1) | 2.1 | °C/W |
| $R_{\theta JA}$ | Thermal Resistance, Junction-to-Ambient | (Note 1a) | 40 | |
| $R_{\theta JA}$ | Thermal Resistance, Junction-to-Ambient | (Note 1b) | 96 | |

## Package Marking and Ordering Information

| Device Marking | Device | Package | Reel Size | Tape width | Quantity |
|---|---|---|---|---|---|
| FDD6682 | FDD6682 | D-PAK (TO-252) | 13'' | 12mm | 2500 units |
| FDU6682 | FDU6682 | I-PAK (TO-251) | Tube | N/A | 75 |

## Electrical Characteristics

$T_A$ = 25°C unless otherwise noted

| Symbol | Parameter | Test Conditions | Min | Typ | Max | Units |
|---|---|---|---|---|---|---|
| **Drain-Source Avalanche Ratings (Note 2)** | | | | | | |
| $W_{DSS}$ | Drain-Source Avalanche Energy | Single Pulse, $V_{DD}$ = 15 V, $I_D$ = 17 A | | | 240 | mJ |
| $I_{AR}$ | Drain-Source Avalanche Current | | | | 17 | A |
| **Off Characteristics** | | | | | | |
| $BV_{DSS}$ | Drain–Source Breakdown Voltage | $V_{GS}$ = 0 V, $I_D$ = 250 µA | 30 | | | V |
| $\frac{\Delta BV_{DSS}}{\Delta T_J}$ | Breakdown Voltage Temperature Coefficient | $I_D$ = 250 µA, Referenced to 25°C | | 20 | | mV/°C |
| $I_{DSS}$ | Zero Gate Voltage Drain Current | $V_{DS}$ = 24 V, $V_{GS}$ = 0 V | | | 1 | µA |
| $I_{GSS}$ | Gate–Body Leakage | $V_{GS}$ = ±20 V, $V_{DS}$ = 0 V | | | ±100 | nA |
| **On Characteristics (Note 2)** | | | | | | |
| $V_{GS(th)}$ | Gate Threshold Voltage | $V_{DS}$ = $V_{GS}$, $I_D$ = 250 µA | 1 | 1.9 | 3 | V |
| $\frac{\Delta V_{GS(th)}}{\Delta T_J}$ | Gate Threshold Voltage Temperature Coefficient | $I_D$ = 250 µA, Referenced to 25°C | | –7 | | mV/°C |
| $R_{DS(on)}$ | Static Drain–Source On–Resistance | $V_{GS}$ = 10 V, $I_D$ = 17 A<br>$V_{GS}$ = 4.5 V, $I_D$ = 15 A<br>$V_{GS}$ = 10 V, $I_D$ = 17 A, $T_J$=125°C | | 5.2<br>6.4<br>8.0 | 6.2<br>8<br>11.9 | mΩ |
| $I_{D(on)}$ | On–State Drain Current | $V_{GS}$ = 10 V, $V_{DS}$ = 5 V | 50 | | | A |
| $g_{FS}$ | Forward Transconductance | $V_{DS}$ = 5 V, $I_D$ = 17 A | | 65 | | S |
| **Dynamic Characteristics** | | | | | | |
| $C_{iss}$ | Input Capacitance | $V_{DS}$ = 15 V, $V_{GS}$ = 0 V, f = 1.0 MHz | | 2400 | | pF |
| $C_{oss}$ | Output Capacitance | | | 577 | | pF |
| $C_{rss}$ | Reverse Transfer Capacitance | | | 258 | | pF |
| $R_G$ | Gate Resistance | $V_{GS}$ = 15 mV, f = 1.0 MHz | | 1.4 | | Ω |
| **Switching Characteristics (Note 2)** | | | | | | |
| $t_{d(on)}$ | Turn–On Delay Time | $V_{DD}$ = 15 V, $I_D$ = 1 A, $V_{GS}$ = 10 V, $R_{GEN}$ = 6 Ω | | 14 | 20 | ns |
| $t_r$ | Turn–On Rise Time | | | 12 | 37 | ns |
| $t_{d(off)}$ | Turn–Off Delay Time | | | 38 | 64 | ns |
| $t_f$ | Turn–Off Fall Time | | | 18 | 32 | ns |
| $Q_g$ | Total Gate Charge | $V_{DS}$ = 15V, $I_D$ = 17 A, $V_{GS}$ = 5 V | | 24 | 31 | nC |
| $Q_{gs}$ | Gate–Source Charge | | | 6.5 | | nC |
| $Q_{gd}$ | Gate–Drain Charge | | | 8.1 | | nC |

## Electrical Characteristics (continued)

$T_A$ = 25°C unless otherwise noted

| Symbol | Parameter | Test Conditions | Min | Typ | Max | Units |
|---|---|---|---|---|---|---|
| **Drain–Source Diode Characteristics and Maximum Ratings** | | | | | | |
| $I_S$ | Maximum Continuous Drain–Source Diode Forward Current | | | | 3.2 | A |
| $V_{SD}$ | Drain–Source Diode Forward Voltage | $V_{GS}$ = 0 V, $I_S$ = 3.2 A (Note 2) | | 0.7 | 1.2 | V |
| $t_{rr}$ | Diode Reverse Recovery Time | $I_F$ = 17 A, $d_{iF}/d_t$ = 100 A/µs | | 32 | | nS |
| $Q_{rr}$ | Diode Reverse Recovery Charge | | | 20 | | nC |

**Notes:**

**1.** $R_{\theta JA}$ is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins. $R_{\theta JC}$ is guaranteed by design while $R_{\theta CA}$ is determined by the user's board design.

a) $R_{\theta JA}$ = 40°C/W when mounted on a 1in$^2$ pad of 2 oz copper

b) $R_{\theta JA}$ = 96°C/W when mounted on a minimum pad.

Scale 1 : 1 on letter size paper

**2.** Pulse Test: Pulse Width < 300µs, Duty Cycle < 2.0%

**3.** Maximum current is calculated as: $\sqrt{\frac{P_D}{R_{DS(ON)}}}$

where $P_D$ is maximum power dissipation at $T_C$ = 25°C and $R_{DS(on)}$ is at $T_{J(max)}$ and $V_{GS}$ = 10V. Package current limitation is 21A

## Typical Characteristics

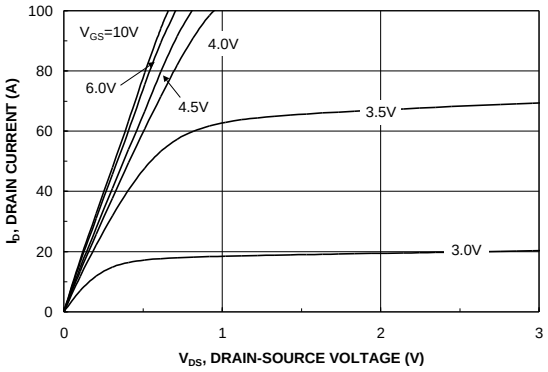



**Figure 1. On-Region Characteristics.**

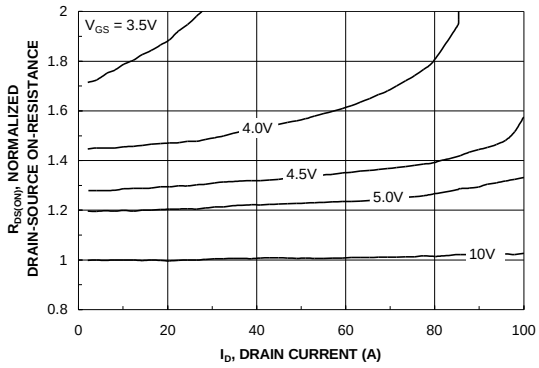



**Figure 2. On-Resistance Variation with Drain Current and Gate Voltage.**

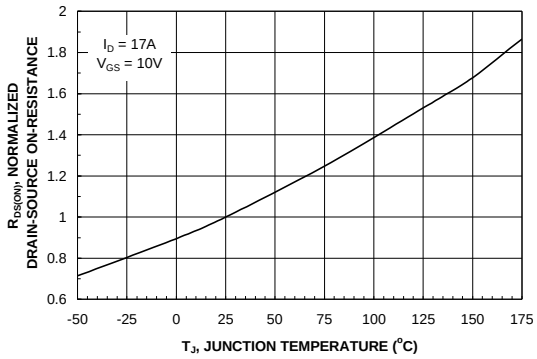



**Figure 3. On-Resistance Variation with Temperature.**

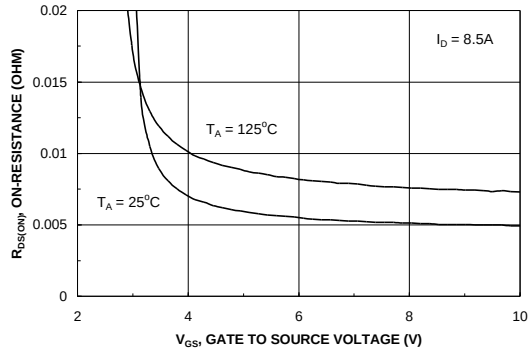



**Figure 4. On-Resistance Variation with Gate-to-Source Voltage.**

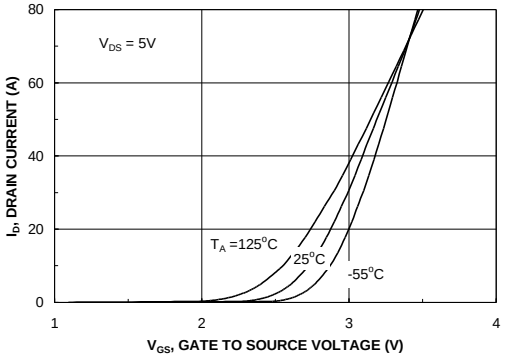



**Figure 5. Transfer Characteristics**

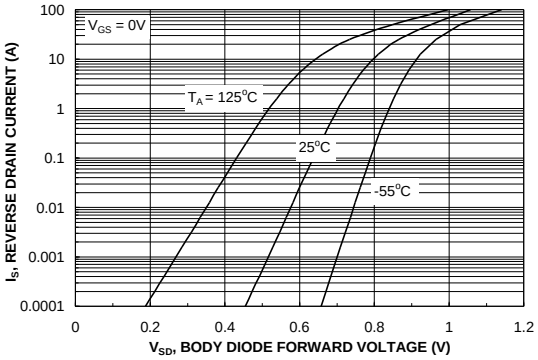



**Figure 6. Body Diode Forward Voltage Variation with Source Current and Temperature**